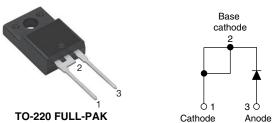


### VS-30ETH06FP-F3, VS-30ETH06FP-N3

Vishay Semiconductors

## Hyperfast Rectifier, 30 A FRED Pt®



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#### **FEATURES**

- Reduced Q<sub>rr</sub> and soft recovery
- 175 °C T<sub>J</sub> maximum
- For PFC CRM/CCM operation
- Fully isolated package (V<sub>INS</sub> = 2500 V<sub>RMS</sub>)
- UL E78996 approved



· Designed and qualified according to JEDĔC®-JESD 47







RoHS HALOGEN **FREE** 

#### **DESCRIPTION / APPLICATIONS**

State of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recovery time and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC boost stage in the AC/DC section of SMPS, inverters or as freewheeling diodes.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

PRODUCT SUMMARY				
Package	TO-220FP			
I <sub>F(AV)</sub>	30 A			
V <sub>R</sub>	600 V			
V <sub>F</sub> at I <sub>F</sub>	1.34 V			
t <sub>rr</sub> (typ.)	23 ns			
T <sub>J</sub> max.	175 °C			
Diode variation	Single die			
·				

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Peak repetitive reverse voltage	$V_{RRM}$		600	V		
Average rectified forward current	I <sub>F(AV)</sub>	T <sub>C</sub> = 37 °C	30	Δ.		
Non-repetitive peak surge current	I <sub>FSM</sub>	T <sub>J</sub> = 25 °C	220	A		
Operating junction and storage temperatures	T <sub>J</sub> , T <sub>Stg</sub>		-65 to +175	°C		

<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	V <sub>BR</sub> , V <sub>R</sub>	Ι <sub>R</sub> = 100 μΑ	600	-	-	
Forward voltage V <sub>F</sub>	I <sub>F</sub> = 30 A	-	2.00	2.60	V	
	I <sub>F</sub> = 30 A, T <sub>J</sub> = 150 °C	-	1.34	1.75		
Poverse leekage ourrent		$V_R = V_R$ rated	-	0.3	50	
Reverse leakage current I <sub>R</sub>		T <sub>J</sub> = 150 °C, V <sub>R</sub> = V <sub>R</sub> rated	-	60	500	μΑ
Junction capacitance	C <sub>T</sub>	V <sub>R</sub> = 600 V	1	33	-	pF
Series inductance	L <sub>S</sub>	Measured lead to lead 5 mm from package body	-	8	-	nΗ



# **VS-30ETH06FP-F3, VS-30ETH06FP-N3**

## Vishay Semiconductors

<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
		$I_F = 1 \text{ A}, dI_F/dt = 50$	0 A/μs, V <sub>R</sub> = 30 V	-	28	35	
Poverse recovery time	everse recovery time t <sub>rr</sub>	$I_F = 1 \text{ A}, dI_F/dt = 100 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		-	23	30	ns
neverse recovery time		T <sub>J</sub> = 25 °C		-	31	-	115
		T <sub>J</sub> = 125 °C		-	77	-	
Dook roopyony ourront	Peak recovery current I <sub>RRM</sub>	T <sub>J</sub> = 25 °C	$I_F = 30 \text{ A}$	-	3.5	-	А
Peak recovery current		T <sub>J</sub> = 125 °C	dl <sub>F</sub> /dt = 200 A/µs V <sub>R</sub> = 200 V	-	7.7	-	
D	0	T <sub>J</sub> = 25 °C		-	65	-	nC
Reverse recovery charge	Q <sub>rr</sub>	T <sub>J</sub> = 125 °C		-	345	-	nc nc

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-65	-	175	°C
Thermal resistance, junction to case per leg	R <sub>thJC</sub>		-	-	2.85	
Thermal resistance, junction to ambient per leg	R <sub>thJA</sub>	Typical socket mount	-	-	70	°C/W
Thermal resistance, case to heatsink	R <sub>thCS</sub>	Mounting surface, flat, smooth and greased	-	0.2	-	
Weight			-	2	-	g
vveigni			-	0.07	-	oz.
Mounting torque			6 (5)	-	12 (10)	kgf · cm (lbf · in)
Marking device		Case style TO-220 FULL-PAK		30ETH	H06FP	•



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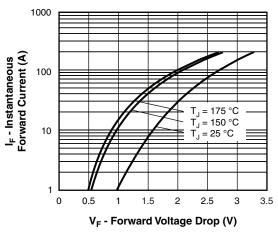


Fig. 1 - Typical Forward Voltage Drop Characteristics

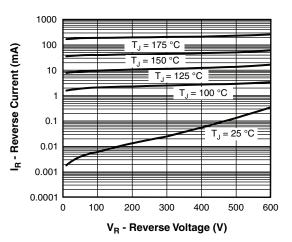


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

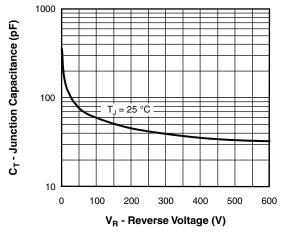


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

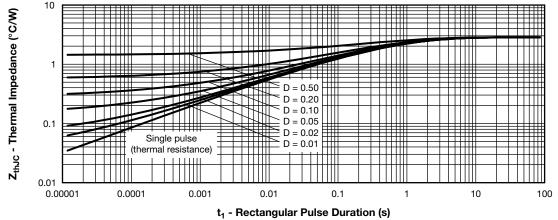


Fig. 4 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics





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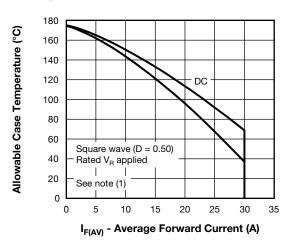


Fig. 5 - Maximum Allowable Case Temperature vs.
Average Forward Current

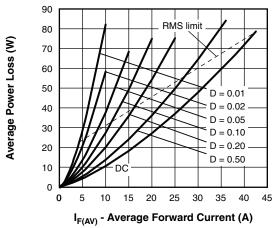


Fig. 6 - Forward Power Loss Characteristics

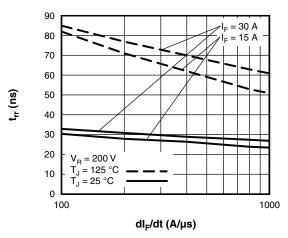


Fig. 7 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

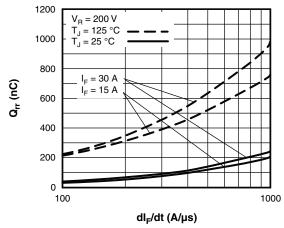


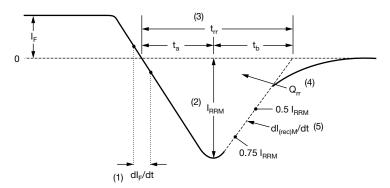
Fig. 8 - Typical Stored Charge vs. dl<sub>F</sub>/dt

#### Note

 $\begin{array}{l} \text{(1)} \ \ \text{Formula used:} \ T_C = T_J - (Pd + Pd_{REV}) \times R_{th,JC}; \\ Pd = \text{Forward power loss} = I_{F(AV)} \times V_{FM} \ \text{at } (I_{F(AV)}/D) \ \text{(see fig. 6)}; \\ Pd_{REV} = \text{Inverse power loss} = V_{R1} \times I_R \ \text{(1 - D)}; \ I_R \ \text{at } V_{R1} = \text{Rated } V_R \\ \end{array}$ 

## VS-30ETH06FP-F3, VS-30ETH06FP-N3

### Vishay Semiconductors

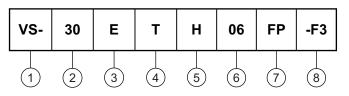


- (1) dl<sub>F</sub>/dt rate of change of current through zero crossing
- (4)  $Q_{rr}$  area under curve defined by  $t_{rr}$  and  $I_{RRM}$
- (2) I<sub>RRM</sub> peak reverse recovery current
- $Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$
- (3) t<sub>rr</sub> reverse recovery time measured from zero crossing point of negative going I<sub>F</sub> to point where a line passing through 0.75 I<sub>RRM</sub> and 0.50 I<sub>RRM</sub> extrapolated to zero current.
- (5) dl<sub>(rec)M</sub>/dt peak rate of change of current during t<sub>b</sub> portion of t<sub>rr</sub>

Fig. 9 - Reverse Recovery Waveform and Definitions

#### **ORDERING INFORMATION TABLE**

**Device code** 



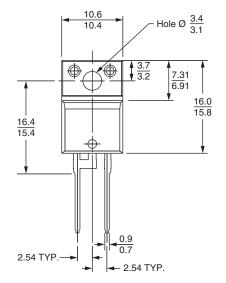
- Vishay Semiconductors product
- 2 Current rating (30 A)
- 3 E = single diode
- **4** T = TO-220
- 5 H = hyperfast recovery
- Voltage rating (06 = 600 V)
- 7 FULL-PAK
- 8 Environmental digit:
  - -F3 = RoHS-compliant and totally lead (Pb)-free
  - -N3 = halogen-free, RoHS-compliant and totally lead (Pb)-free

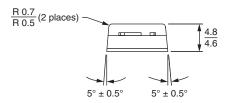
ORDERING INFORMATION (Example)					
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION		
VS-30ETH06FP-F3	50	1000	Antistatic plastic tube		
VS-30ETH06FP-N3	50	1000	Antistatic plastic tube		

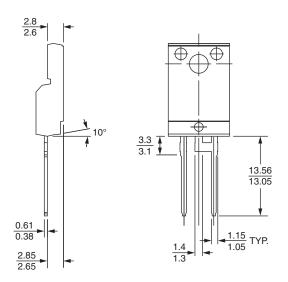
LINKS TO RELATED DOCUMENTS					
Dimensions <u>www.vishay.com/doc?95005</u>					
Part marking information	www.vishay.com/doc?95440				

### Vishay Semiconductors

#### **DIMENSIONS** in millimeters







#### Lead assignments

<u>Diodes</u> 1 + 2 - Cathode 3 - Anode

Conforms to JEDEC outline TO-220 FULL-PAK



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